- 1 1. A method comprising:
- 2 exposing a contact plug fill to an etching
- 3 solution; and
- 4 determining if the region under the contact plug
- 5 fill is etched away.
- 1 2. The method of claim 1 including exposing the
- 2 contact plug fill to a basic solution.
- 1 3. The method of claim 1 including exposing the
- 2 contact plug fill to a solution that preferably etches
- 3 along the <111> crystallographic orientation
- 1 4. The method of claim 1 including using an etching
- 2 solution that etches a characteristic etch pattern under
- 3 the contact plug fill if the contact plug fill is
- 4 defective.
- 1 5. The method of claim 1 including exposing the
- 2 surface of said contact plug fill to an electrical charge.
- 1 6. The method of claim 5 including exposing said
- 2 surface to charge using voltage contrast-based defect
- 3 inspection.

- 1 7. The method of claim 5 including applying a
- 2 contact to said contact plug fill to enable electrical
- 3 testing of the contact plug fill.
- 1 8. The method of claim 5 including determining which
- 2 contact plug fill dissipates surface charge and which
- 3 contact plug fill does not dissipate surface charge.
- 9. A method comprising:
- 2 forming a conductive material in an aperture in a
- 3 dielectric layer; and
- 4 applying an etching solution to said conductive
- 5 material to determine whether the conductive material is
- 6 defective.
- 1 10. The method of claim 9 including exposing a
- 2 contact plug fill to an etching solution.
- 1 11. The method of claim 9 including applying an
- 2 etching solution which characteristically etches underneath
- 3 the conductive material if the conductive material is
- 4 defective.
- 1 12. The method of claim 9 including applying a basic
- 2 solution to said conductive material.

- 1 13. The method of claim 9 wherein applying an etching
- 2 solution includes exposing the conductive material to a
- 3 solution that preferentially etches along the <111>
- 4 crystallographic direction.
- 1 14. The method of claim 12 including applying an
- 2 etching solution that etches a V-shaped trench under a
- 3 defective conductive material.
- 1 15. The method of claim 9 including exposing the
- 2 surface of said conductive material to an electric charge.
- 1 16. The method of claim 15 including using voltage
- 2 contrast-based defect inspection.
- 1 17. The method of claim 9 including applying a
- 2 contact to said conductive material.
- 1 18. The method of claim 17 including using electrical
- 2 testing to determine if said conductive material is
- 3 defective.
- 1 19. The method of claim 15 including using a
- 2 secondary electron image to determine if said conductive
- 3 material is defective.

- 1 20. A method comprising:
- 2 forming a contact plug fill in a dielectric
- 3 layer;
- 4 applying a basic solution to said contact plug
- 5 fill; and
- 6 determining whether the region underneath the
- 7 contact plug fill is etched by said basic solution.
- 1 21. The method of claim 20 including applying a basic
- 2 solution which characteristically etches underneath the
- 3 contact plug fill if the fill is defective.
- 1 22. The method of claim 20 wherein applying a basic
- 2 solution includes exposing the contact plug fill to a
- 3 solution that preferentially etches along the <111>
- 4 crystallographic direction.
- 1 23. The method of claim 21 including applying a basic
- 2 solution that etches a V-shaped trench under a defective
- 3 fill.
- 1 24. The method of claim 20 including exposing the
- 2 contact plug fill to an electric charge.
- 1 25. The method of claim 24 including using voltage
- 2 contrast-based defect inspection.

- 1 26. The method of claim 20 including applying a
- 2 contact to said contact plug fill.
- 1 27. The method of claim 21 including using electrical
- 2 testing to determine if said fill is defective.
- 1 28. The method of claim 24 including using a
- 2 secondary electron image to determine if said fill is
- 3 defective.